



# 《风光欣》技术资料

\*\*\*\*\*

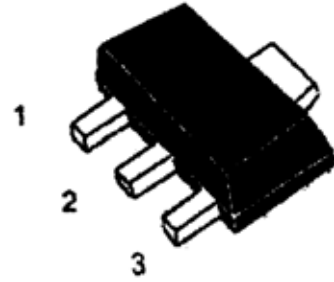
## 2SB1124

PNP EPITAXIAL SILICON TRANSISTOR

### Applications

· Voltage regulators, relay drivers, lamp drivers,  
electrical equipment.

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter -Base Voltage	$V_{EBO}$	-6	V
Collector Current (DC)	$I_c$	-3	A
Collector Current (Pulse)	$I_c$	-6	A
Collector Dissipation ( $T_c=25$ )	$P_c$	500	mW
Collector Dissipation ( $T_a=25$ )	$P_c$	1.5	W
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{STG}$	-55 ~150	



1,Base 2,Collector 3,Emitter

### ELECTRICAL CHARACTERISTICS( $T_a=25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cutoff Current	$I_{CB0}$	$V_{CB} = -40V, I_E = 0$			-1	$\mu A$
Emitter-Cutoff Current	$I_{EB0}$	$V_{EB} = -4V, I_c = 0$			-1	$\mu A$
*DC Current Gain	$h_{FE1}$	$V_{CE} = -2V, I_c = -100mA$	100		560	
	$h_{FE2}$	$V_{CE} = -2V, I_c = -3A$	35			
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -2A, I_B = -100mA$		-0.35	-0.7	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -2A, I_B = -100mA$		-0.94	-1.2	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = -10V, I_E = -50mA$		150		MHZ
Output Capacitance	$C_{OB}$	$V_{CB} = -10V, f = 1MHz$		39		pF

Turn-ON Time	$t_{on}$	See specified Test Circuit.		70		ns
				(70)		ns
Storage Time	$t_{stg}$	See specified Test Circuit.		650		ns
				(450)		ns
Fall Time	$t_f$	See specified Test Circuit.		35		ns
				(35)		ns

### HFE CLASSIFICATION

Classification	R	S	T	U
HFE	100-200	140-280	200-400	280-560